## Charge D ynam ics from C opper O xide M aterials

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The charge dynam ics of the copper oxide m aterials in the underdoped and optim al doped regimes is studied within the framework of the ferm ion-spin theory. The conductivity spectrum shows the non-D rude behavior at low energies and unusual m idinfrared peak, and the resistivity exhibits a linear behavior in the tem perature, which are consistent with experiments and numerical simulations.

71.27.+a, 72.10.-d, 74.72.-h

Since the discovery of the copper oxide superconductors, a signi cant body of reliable and reproducible data has been accumulated by using many probes [1], which show that the m ost remarkable expression of nonconventional physics of copper oxide materials is found in the norm al-state. The norm al-state properties exhibit a num ber of anom abus properties in sense that they do not t in the conventional Ferm i-liquid theory, and some properties mainly depend on the extend of dopings [1]. The undoped copper oxide materials are antiferrom agnetic M ott insulators, and the antiferrom agnetic long-range-order (AFLRO) disappears when the hole doping concentration exceeds som e critical value (about 5%) [2]. The charge response in the underdoped and optim aldoped regimes, as manifested by the optical conductivity and resistivity, has been extensively studied experimentally in the copper oxide m aterials, as well as theoretically within some strongly correlated m odels  $\beta$ {7]. From experim ents testing norm al-state properties, the optical conductivity shows the non-D rude behavior at low energies and anom alous midinfrared band in the charge-transfer gap, the resistivity exhibits a linear behavior in the tem perature in the optim al doped regime and a nearly tem perature linear dependence with deviations at low tem peratures in the underdoped regime [1,3,4]. These optical properties indicate that the strong correlations are very in portant to the electronic structure.

Am ong the m icroscopic m odels the m ost helpful for the discussion of the norm al-state properties in the copper oxide m aterials is the t-J m odel acting on the space with no doubly occupied sites [8]. In order to account for real experiments under the t-J m odel, the crucial requirement is to impose the electron local constraint [9]. Recently a ferm ion-spin theory based on the charge-spin separation is proposed [10] to incorporated this constraint. In this approach, the electron on-site local constraint for single occupancy is satisfied even in the m ean-eld approximation (MFA). Within the ferm ion-spin theory, it has been shown [11] that AFLRO vanishes around doping = 5% for the reasonable value of the parameter t=J = 5, and the mean-eld theory [12] in the underdoped and optim al doped regimes without AFLRO has been also developed, which has been applied to study the photoem ission and electron dispersion. In this paper, we try to study the charge dynam ics of the copper oxide

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m aterials within this ferm ion-spin theory. We follow the ferm ion-spin form ulism [10,12] and decompose the electron operators as  $C_{i''} = h_i^y S_i$  and  $C_{i\#} = h_i^y S_i^+$ , where the spinless ferm ion operator  $h_i$  keeps track of the charge (holon), while the pseudospin operator  $S_i$  keeps track of the spin (spinon). The mean- eld order parameters are de ned [12] as  $= h_2^{\varphi} S_{i+}^-$  i = $hS_i S_{i+}^+ i$ ,  $_z = hS_i^z S_{i+}^z i$ ,  $C = (1=Z^2)^P$ ;  $_0hS_{i+}^+ S_{i+-0}i$ ,  $C_z = (1=Z^2)^P$ ;  $_0hS_{i+}^z S_{i+-0}^z i$ , and  $= hh_i^y h_{i+-}^y i$  with  $^- = x$ ;  $\hat{y}$ , and Z is the number of nearest neighbor sites. In this case, the low-energy behavior can be described [12] by the elective H am iltonian  $H = H_t + H_J$ with

$$H_{t} = t_{i}^{X} h_{i}h_{i^{+}}^{Y} (S_{i}^{+}S_{i^{+}} + S_{i}S_{i^{+}}^{+}) + hc^{+} h_{i}^{X} h_{i}^{Y}h_{i};$$
(1a)

$$H_{J} = J_{eff} \int_{i}^{X} \left[ \frac{1}{2} (S_{i}^{+} S_{i+} + S_{i} S_{i+}^{+}) + S_{i}^{z} S_{i+}^{z} \right];$$
(1b)

where  $J_{eff} = J[(1)^2 - i]$ , and is the chemical potential which enforce  $h_i^y h_i i =$ 

The spinon and holon may be separated at mean-eld level, but they are strongly coupled beyond MFA due to uctuations [13]. For discussing the optical conductivity and resistivity, we now need to consider the dynamical e ects beyond MFA. Since an electron is represented by the product of a holon and a spinon in the ferm ion-spin theory [10,12], the external eld can only be coupled to one of them. A coording to Io e-Larkin combination rule [14], we can separately calculate the contributions to the conductivity from holons  $_{\rm h}$  (!) and spinons  $_{\rm s}$  (!), and the total conductivity is given by  $1 (!) = \prod_{h=1}^{1} (!) + \prod_{s=1}^{1} (!)$ . In the present theoretical fram ework, the current densities of spinons and holons are dened as  $j = te^{P_{i}} \wedge (S_{i}^{+}S_{i+} + S_{i}S_{i+}^{+})$  and  $j_{h} = 2te^{P_{i}} \wedge h_{i+}^{y} h_{i+}$ respectively. A formal calculation for the spinon part shows that there is no the direct contribution to the current-current correlation from spinons, but the strongly correlation between holons and spinons is considered through the spinon's order parameters , C , and C  $_{\rm z}$  entering in the holon part of the contribution to the current-current correlation, which means that the holon moves in the background of spinons, and the cloud of distorted spinon background is to follow holons, therefore the dressing of the holon by spinon excitations is the key ingredient in the explanation of the transport property. In

this case, the conductivity is expressed as  $(!) = \text{Im}_{h}(!) = ! \text{ with the holon-holon correlation function}_{h}(i!_{n}) = (2\text{te Z})^{2}(1=N)^{P}_{k} _{sk}^{2}(1=)^{P}_{i!_{m}0} g(k;i!_{m}0 + i!_{n})g(k;i!_{m}0),$ where  $_{sk} = (1=2)(\text{sink}_{x} + \text{sink}_{y})$  and the holon G reen's function is de ned as  $q_{j}( ^{0}) =$ 

hT h<sub>i</sub>() $h_{j}^{v}$ (°)i. In this paper, we limit the spinon part to the rst-order (mean-eki level) since some physical properties can be well described at this level [12], and there is no direct contribution to the charge dynamics from spinons as mentioned above. However, the second-order correction for the holon is necessary for a proper description of holon motion due to antiferrom agnetic uctuations. The mean-eki spinon G reen's functions  $D^{(0)}$  (k;!) and mean-eki holon G reen's function  $g^{(0)}$  (k;!) have been given in Ref. [12]. The second-order holon self-energy diagram from the spinon pair bubble is shown in Fig. 1. Since the spinon operators obey the Paulialgebra, we map the spinon operator into the CP<sup>1</sup> ferm ion representation or spinless-ferm ion representation expansion. A fler then the spinon G reen's function  $D^{(0)}$  (k;!), and therefore the second-order holon self-energy diagram shown in Fig. 1 is replaced by the mean-eki spin G reen's function  $D^{(0)}$  (k;!), and therefore the second-order holon self-energy diagram shown in Fig. 1 is replaced by the

$$\frac{{}_{h}^{(2)}(k;!) = (Z t)^{2} \frac{1}{N^{2}} \sum_{pp^{0}}^{X} (p^{0} k + p^{0} p + p^{k})^{2} B_{p^{0}} B_{p+p^{0}} }{2 \frac{n_{F}(p+k) [n_{B}(!p^{0}) - n_{B}(!p+p^{0})] - n_{B}(!p+p^{0}) n_{B}(!p+p^{0})}{1 + !p + p^{0} + !p^{0} - p + k + i0^{+}} }$$

$$+ \frac{n_{F}(p+k) [n_{B}(!p+p^{0}) - n_{B}(!p^{0})] + n_{B}(!p^{0}) n_{B}(!p+p^{0})}{1 + !p^{0} + !p + p^{0} - p + k + i0^{+}} }{\frac{n_{F}(p+k) [n_{B}(!p+p^{0}) - n_{B}(!p^{0})] - n_{B}(!p^{0}) n_{B}(!p+p^{0})}{1 + !p + p^{0} - p + k + i0^{+}}} ;$$

$$(2)$$

where  $_{k} = (1=Z)^{P} e^{ik}$ ,  $= 1 + 2t = J_{eff}$ ,  $B_{k} = Z J_{eff} [(2_{z} + )_{k} (+2_{z})] = !_{k}$ ,  $n_{F} (_{k})$  and  $n_{B} (!_{k})$  are the Ferm i and Bose distribution functions, respectively, the meaneld holon excitation spectrum  $_{k} = 2Z t_{k} +$ , and the mean- eld spinon excitation spectrum  $!_{k}$  is given in Ref. [12]. Then the full holon G reen's function is obtained as  $g^{1} (k; !) = g^{(0) 1} (k; !) = {}^{(2)}_{h} (k; !)$ . We emphasize that the local constraint of the t-J m odel has been treated exactly in the mean- eld theory [12], and it is still satisfies ed in the above perturbation expansion based on this mean-eld theory.

W ith the help of the full holon G reen's function, the optical conductivity can be obtained as

$$(!) = \frac{1}{2} (2 \text{te } Z)^{2} \frac{1}{N} \sum_{k}^{X} \sum_{i=1}^{2} \frac{1}{2} \frac{d!^{0}}{2} A_{h} (k; !^{0} + !) A_{h} (k; !^{0}) \frac{n_{F} (!^{0} + !) n_{F} (!^{0})}{!}; \qquad (3)$$

with the holon spectral function  $A_h(k;!) = 2 \text{Im } g(k;!)$ . We have perform ed a num erical calculation for this optical conductivity (3), and the results at the doping = 0.06 (solid = 0:12 (dashed line) for the parameter t=J = 2.5 with the tem perature T = 0line) and are shown in Fig. 2, where the charge e has been set as the unit. For comparison, the result from num erical simulation based on the Lanczos diagonalization [5] of a 4 4 cluster with a single doped hole (0.06) for t=J = 2.0 is also shown in Fig 2 (dot-dashed line). A lthough the infrared properties of the copper oxide m aterials are very com plicated, som e qualitative features such as away from half- lling, weight appears inside the charge-transfer gap of the undoped m aterials, de ning the midinfrared band and the conductivity decays as ! 1=! at low energies, seem common to all copper oxide materials [1,3,4]. The present theoretical result shows that there are a low-energy peak at ! < 0.5t separated by a gap or pseudogap 0.5t from the broad absorption band (midinfrared band) in the conductivity spectrum. The analysis of the result indicates that the conductivity decays is ! 1=! (non-D rude fallo ) at low energies (! < 0.5t), the m idinframed peak is doping dependent and the peak is shifted to lower energy with increased doping, which is in qualitative agreem ent with the experim ent [4] and num erical simulation [5,6].

It has been shown that the D nude weight can be used as an order parameter for metalinsulator transitions [16], which converges exponentially to zero for the insulator, and nonzero constant for the metal. Following the standard discussions [17], the D nude weight D is obtained in the present case as

$$D_{n} = \frac{h T i}{4} + \lim_{i!_{n}!_{0}} (2 t)^{2} \frac{1}{N} \sum_{k}^{X} \sin^{2} k_{x} \sum_{1}^{2} \frac{d!}{2} \frac{d!}{2} A_{h} (k;!) A_{h} (k;!) \frac{n_{F} (!^{0}) n_{F} (!)}{i!_{n} + !^{0} !}; \quad (4)$$

where  $D_n = D = 2e^2$ , and the total kinetic energy per site hT i = 8t . The numerical results of eq. (4) for t=J = 2.5 (solid line) is plotted in Fig 3. The result shows that the

D rude weight grows rapidly with increasing doping , and the doping dependence is nearly linear in the underdoped and optimal doped regimes, which is qualitative consistent with the exact diagonalization result [18].

The resistivity is expressed as  $= 1 = _{dc}$ , where the dc conductivity  $_{dc}$  is obtained from Eq. (3) as  $_{dc} = \lim_{t \ge 0}$  (!). This resistivity has been evaluated numerically and the results in the doping = 0.06 and = 0.10 for t=J = 2.5 are plotted in Fig. 4 (a) and Fig. 4 (b), respectively, which show that in the underdoping, the resistivity indeed exhibits a nearly tem perature linear dependence with deviations at low tem perature, and a very good linear behavior in the optim all doping, which also is in agreem ent with the experiments [1,3,4].

In the present theory, the basic low energy excitations are holons and spinons. However, our results show that the unusual non-D rude type optical behavior at low energies and m idinfrared band, and linear tem perature dependence of the resistivity are mainly caused by the holons in the copper oxide sheets, which are strongly renormalized because of the interactions with uctuations of the surrounding spinon excitations. The 1=! decay of the conductivity at low energies is closely related with the linear temperature resistivity, this re ects an anom alous frequency dependent scattering rate proportional to ! instead !<sup>2</sup> as would be expected for the conventional Ferm i-liquid theory, which is consistent with the Luttinger-liquid theory [19] and phenom enological marginal Ferm i-liquid theory [20] O ur study seems to con im that the strongly correlated t-J model is possibly su cient for the understanding of the norm al-state properties of the copper oxide materials.

In sum m ary, we have studied the charge dynam ics of the copper oxide m aterials in the underdoped and optim alloped regimes within the t-J m odel. It is shown that the strongly correlated renormalization elects of the holon motion due to spinon uctuations are very important for the charge dynam ics. The optical conductivity, D rude weight and resistivity are discussed, and the results are qualitative consistent with the experiments and numerical simulations.

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## FIGURES

FIG.1. The holon's second-order self-energy diagram. The solid and dashed lines correspond to the holon and spinon propagators, respectively.

FIG.2. The optical conductivity at the doping = 0.06 (solid line) and = 0.12 (dashed line) for t=J = 2.5 with the tem perature T = 0. The dot-dashed line is the result from the num erical simulation on a 4 4 cluster with a single doped hole for t=J = 2.0 [5].

FIG.3. D rude weight, in the unit of t, as a function of doping for t=J = 2.5.

FIG.4. The electron resistivity at the parameter t=J = 2.5 for (a) the doping = 0.06 and (b) = 0.10. The smallwiggles are the nite-size e ect.